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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HD74HC125/HD74HC126

Quad. Bus Buffer Gates (with 3-state outputs)



ADE-205-439 (Z)
1st. Edition
Sep. 2000

Description

The HD74HC125, HD74HC126 require the 3-state control input C to be taken high to put the output into the high impedance condition, whereas the HD74HC125, HD74HC126 requires the control input to be low to put the output into high impedance.

Features

- High Speed Operation: $t_{pd} = 8$ ns typ ($C_L = 50$ pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2$ to 6 V
- Low Input Current: 1 μ A max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max ($T_a = 25^\circ\text{C}$)

Function Table

Inputs

C			Output Y	
HC125	HC126	A	HC125	HC126
H	L	X	Z	Z
L	H	L	L	L
L	H	H	H	H

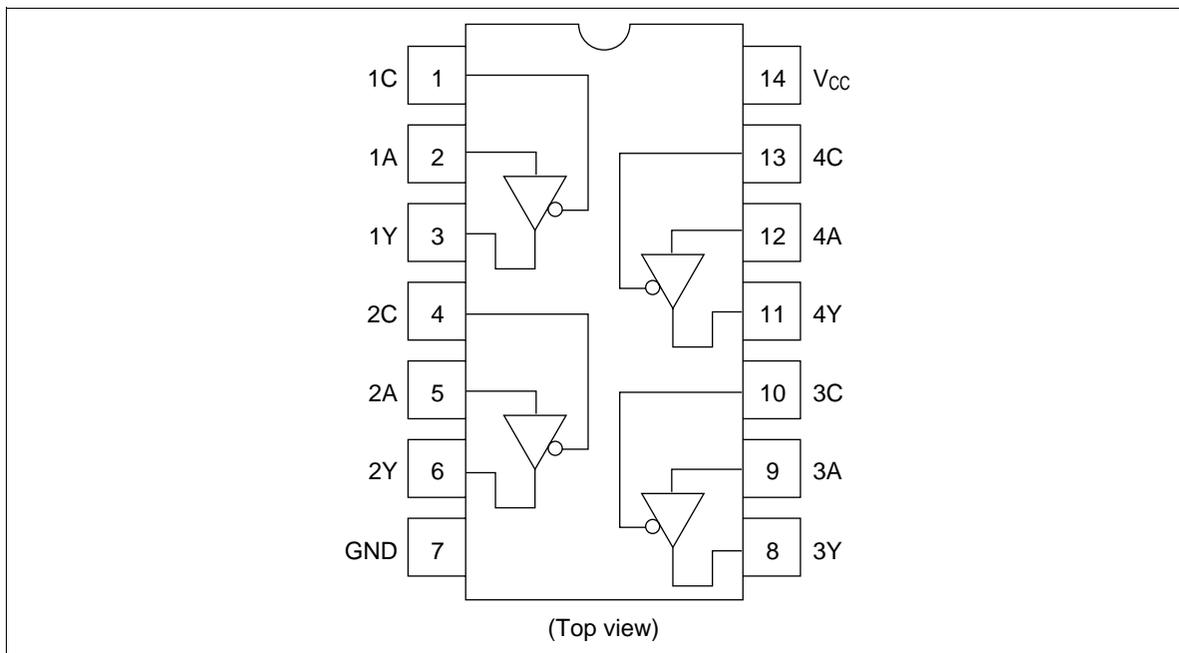
X : Irrelevant

Z : Off (high-impedance) state of a 3-state output.

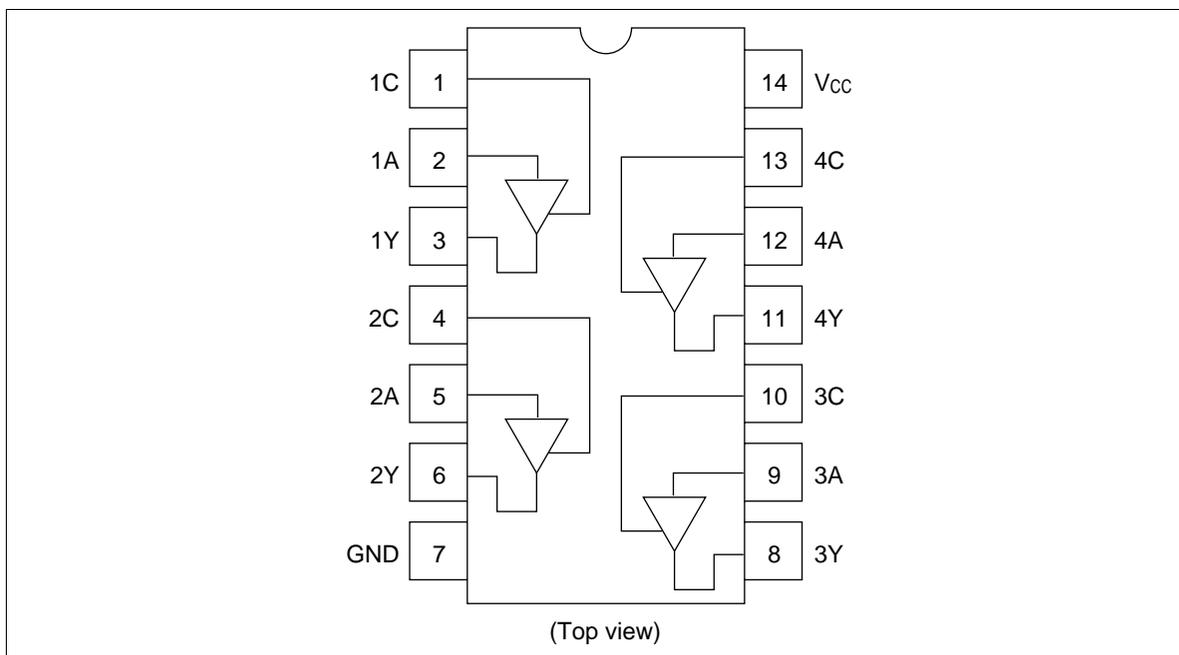
HD74HC125/HD74HC126

Pin Arrangement

HD74HC125



HD74HC126



Absolute Maximum Ratings

Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
Output current	I_{OUT}	± 35	mA
DC current drain per V_{CC} , GND	I_{CC} , I_{GND}	± 75	mA
DC input diode current	I_{IK}	± 20	mA
DC output diode current	I_{OK}	± 20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	Tstg	-65 to +150	$^{\circ}\text{C}$

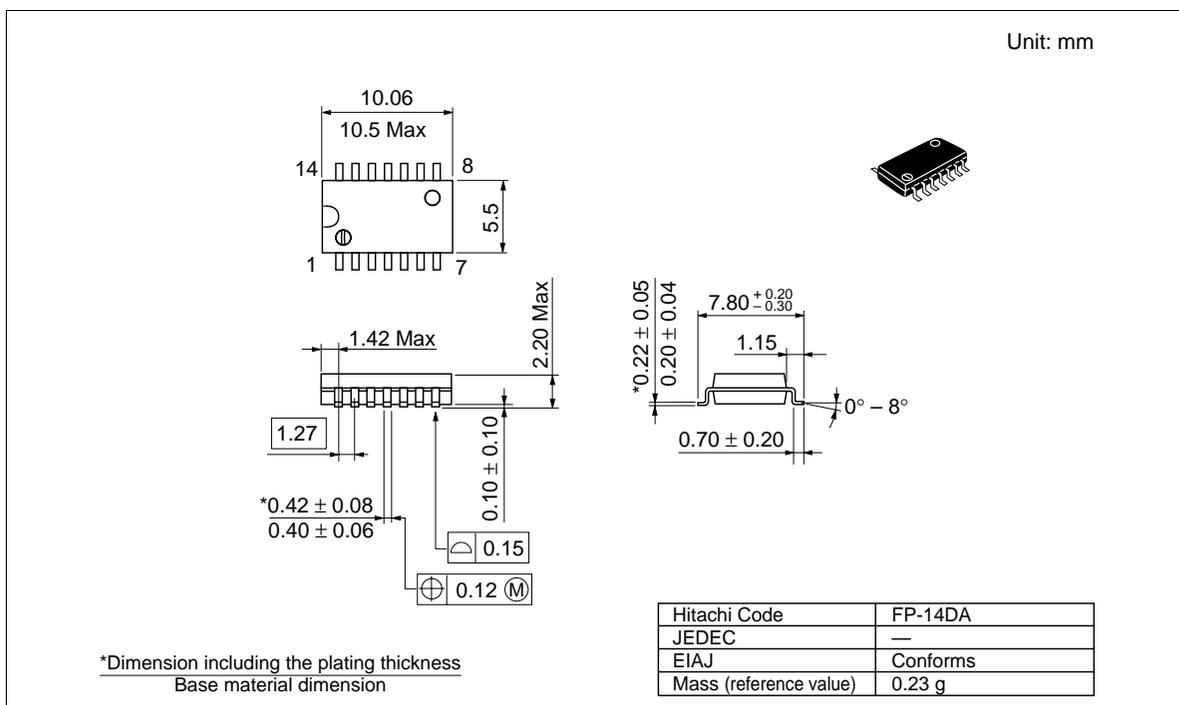
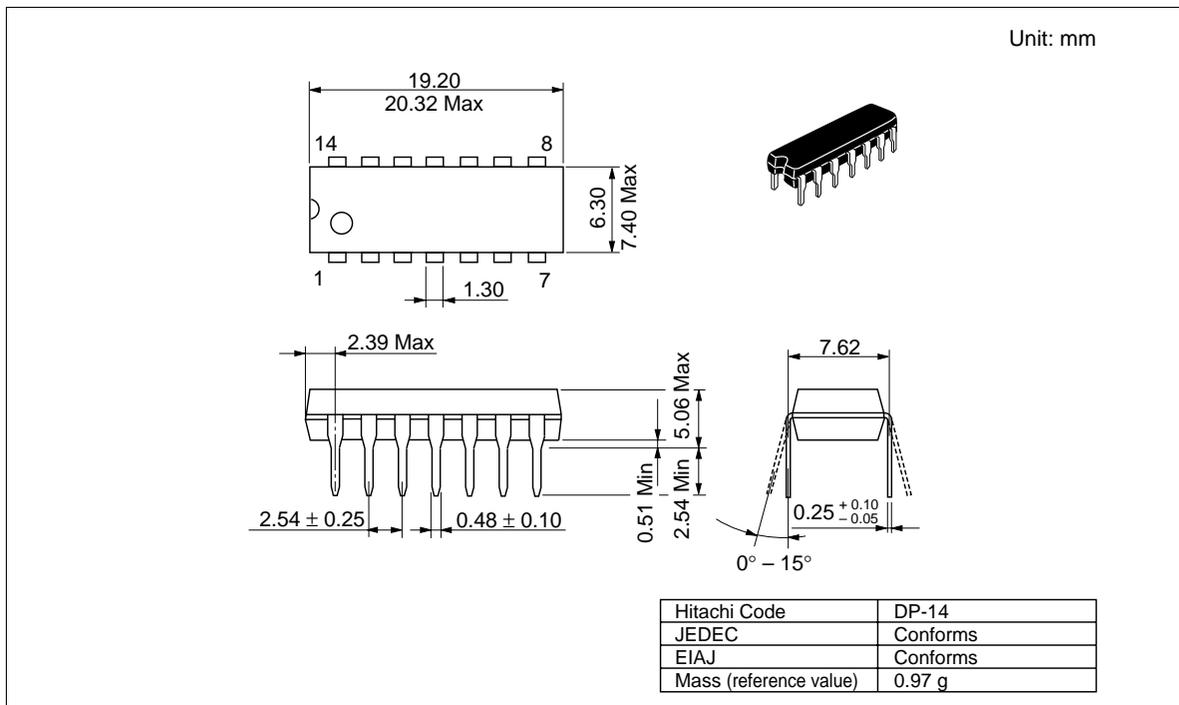
DC Characteristics

Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V _{IL}	2.0	—	—	0.5	—	0.5			V
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V _{IH} or V _{IL} I _{OH} = -20 μA	
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I _{OH} = -6 mA
		6.0	5.68	—	—	5.63	—			I _{OH} = -7.8 mA
	V _{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V _{IH} or V _{IL} I _{OL} = 20 μA	
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I _{OL} = 6 mA
		6.0	—	—	0.26	—	0.33			I _{OL} = 7.8 mA
Off-state output current	I _{OZ}	6.0	—	—	±0.5	—	±5.0	μA	Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND	
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	μA	Vin = V _{CC} or GND	
Quiescent supply current	I _{CC}	6.0	—	—	4.0	—	40	μA	Vin = V _{CC} or GND, Iout = 0 μA	

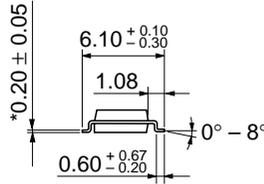
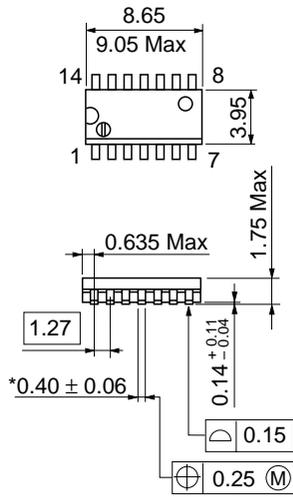
AC Characteristics ($C_L = 50$ pF, Input $t_r = t_f = 6$ ns)

Item	Symbol	V_{CC} (V)	$T_a = 25^\circ\text{C}$			$T_a = -40$ to $+85^\circ\text{C}$		Unit	Test Conditions
			Min	Typ	Max	Min	Max		
Propagation delay time	t_{PLH}	2.0	—	—	100	—	125	ns	
	t_{PHL}	4.5	—	8	20	—	25		
		6.0	—	—	17	—	21		
Output enable time	t_{ZH}	2.0	—	—	150	—	190	ns	
	t_{ZL}	4.5	—	9	30	—	38		
		6.0	—	—	26	—	33		
Output disable time	t_{HZ}	2.0	—	—	150	—	190	ns	
	t_{LZ}	4.5	—	14	30	—	38		
		6.0	—	—	26	—	33		
Output rise/fall time	t_{TLH}	2.0	—	—	60	—	75	ns	
	t_{THL}	4.5	—	4	12	—	15		
		6.0	—	—	10	—	13		
Input capacitance	C_{in}	—	—	5	10	—	10	pF	

Package Dimensions



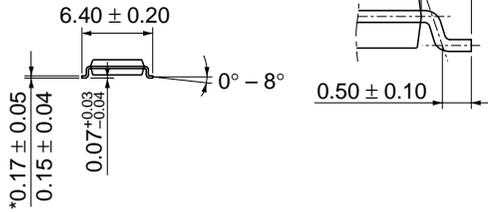
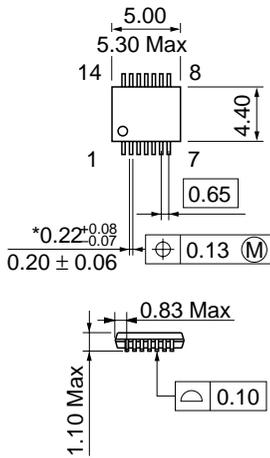
Unit: mm



Hitachi Code	FP-14DN
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.13 g

*Pd plating

Unit: mm



Hitachi Code	TTP-14D
JEDEC	—
EIAJ	—
Mass (reference value)	0.05 g

*Dimension including the plating thickness
Base material dimension

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